									Sheet 1 of 1		
FORM PTO-1449 SAMUELS, GAUTHIER & STEVENS LLP (Rev. 5/92) 225 Franklin Street, Boston, MA 02110 Telephone: (617) 426-9180  INFORMATION DISCLOSURE STATEMENT BY APPLICANT					ATTORNEY DOCKET NO. MIT9888 Pitera et al. APPLICANT: Herewith FILING DATE:			SERIAL NO. Unknown GROUP: Unknown EXAMINER: Unknown			
U.S. PATENT DOCUMENTS											
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME		CLASS	SUBCLASS		FILING DATE IF APPROPRIATE		
BK	AA	5,882,987	3/16/99	Srikrishnan					8/26/97		
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	AH										
•	1	OTHER I	OCUMENTS	(Inclu	ding Author, Title, Dat	e, Pertinent P	ages, Etc.)				
EXAMINER INITIAL	<u> </u>	Gilian Inc	Note: Note: 15	Taska	ala mello M. Daniali T	21	Lattana Is	16 1	1995; Vol. 31, No. 14;		
13K	AI	pgs: 12011202									
BK	AJ .	Applied Physic	"Ge layer transfer to Si for photovoltaic applications"; Zahler et al., Thomas J. Watson Laboratory of Applied Physics, California Institute of Technology; pgs.: 558-562								
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Be	AL	"Electron Mobility Enhancement in Strained-Si n-MOSFETs Fabricated on SiGe-on Insulator (SGOI) Substrates"; Cheng et al., IEEE Electron Device Letters; Vol. 22, No. 7, July 2001; pgs.: 321-323									
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if n t in conformance and not considered. Include copy of this form with next communication to applicant.											

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INFORMATION DISCLOSURE O   STATEMENT BY APPLICANT					FILING DATE: <u>06/25/2003</u>			EXAMINER: Unknown			
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18h	AA	5,462,883	10/31/1995	Dennard et al.			<u> </u>		04/11/1994		
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13K	AH	WO 02/15244	02/21/2002	PCT		•			YES		
you	AI	WO 02/33746	04/25/2002	PCT					YES		
Bu	AJ	WO 02/13342	02/14/2002	PCT				_	YES		
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B	AL	2 777 116	10/08/1999	FR					NO		
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